UP01878

Silicon N-channel MOSFET

For switching

Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

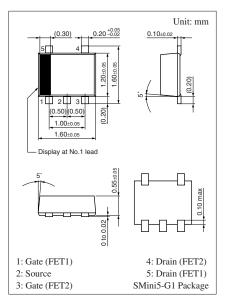
Basic Part Number of Element

• $2SK3539 \times 2$ elements

| | Parameter | Symbol | Rating | Unit | |
|---------|------------------------------------|------------------|-------------|------|--|
| Rating | Drain to source voltage | V _{DSS} | 50 | V | |
| of | Gate to source voltage | V _{GSO} | ±7 | V | |
| element | Drain current | I _D | 100 | mA | |
| | Max drain current | I _{DP} | 200 | mA | |
| Overall | Allowable power dissipation * | P_{D} | 125 | mW | |
| | Channel temperature | T _{ch} | 125 | °C | |
| | Storage temperature | T _{stg} | -55 to +125 | °C | |

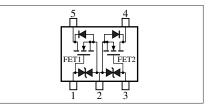
Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Note) *: Total power dissipation | Note) | *: 7 | Гotal | power | dissipation |
|----------------------------------|-------|------|-------|-------|-------------|
|----------------------------------|-------|------|-------|-------|-------------|



Marking Symbol: AL

Internal Connection

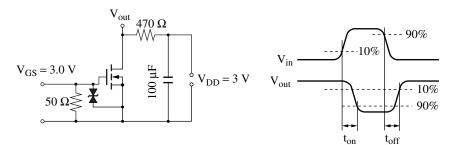


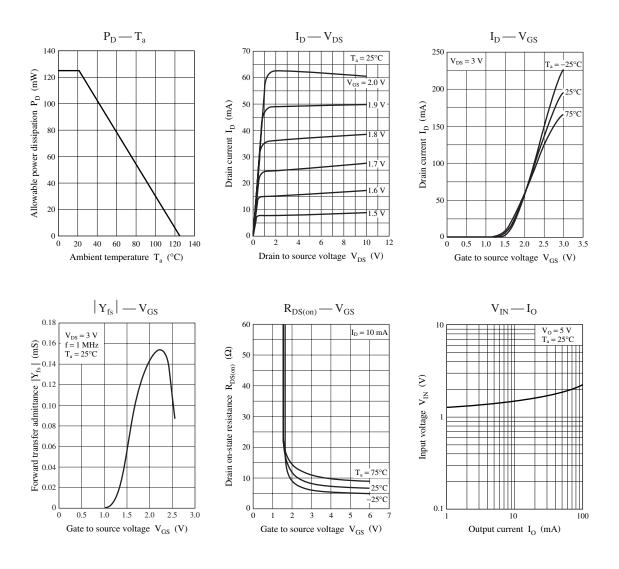
\blacksquare Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|------------------------------|---------------------|--|-----|-----|-----|------|
| Drain to source voltage | V _{DSS} | $I_{\rm D} = 10 \ \mu A, \ V_{\rm GS} = 0$ | 50 | | | V |
| Drain cut-off current | I _{DSS} | $V_{DS} = 50 \text{ V}, V_{GS} = 0$ | | | 1.0 | μΑ |
| Gate cut-off current | I _{GSS} | $V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$ | | | ±5 | μΑ |
| Gate threshold voltage | V _{th} | $I_{\rm D} = 1 \ \mu A, \ V_{\rm DS} = 3 \ V$ | 0.9 | 1.2 | 1.5 | V |
| Drain on-state resistance | R _{DS(on)} | $I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ | | 8 | 15 | Ω |
| | | $I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$ | | 6 | 12 | |
| Forward transfer admittance | Y _{fs} | $I_D = 10 \text{ mA}, V_{DS} = 4.0 \text{ V}$ | 20 | 60 | | mS |
| Input capacitance | C _{iss} | $V_{DS} = 3 V, V_{GS} = 0 V, f = 1 MHz$ | | 12 | | pF |
| Output capacitance | C _{oss} | | | 7 | | pF |
| Reverse transfer capacitance | C _{rss} | | | 3 | | pF |
| Turn-on time * | t _{on} | $V_{DD}{=}3$ V, $V_{GS}{=}0$ V to 3 V, $R_L{=}470\Omega$ | | 200 | | ns |
| Turn-off time * | t _{off} | $V_{DD} = 3 V, V_{GS} = 3 V \text{ to } 0 V, R_L = 470 \Omega$ | | 200 | | ns |

Note) *: Refer to t_{on} , t_{off} test circuit (next page)

ton, toff Test circuit





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